

Notice of References Cited		Application/Control No. 10/612,941	Applicant(s)/Patent Under Reexamination YOON, DONG-SOO	
		Examiner Lisa A Kilday	Art Unit 2829	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
X	A	US-6,274,454 B1	08-2001	Katori, Kenji	438/240
X	B	US-5,122,477 A	06-1992	Wolters et al.	438/396
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Zhan et al., "Characteristics of High Quality Hafnium oxide Gate dielectric", Electron Devices Meeting, 2002., IEEE Hong Kong, 22 June 2002, pp. 43-46
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.